





Replaces DS5886-1.2

Phase Control Thyristor

DS5886-2	August 2022	(LN42024)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		Tvj = -40°С to 125°С, Ідгм = Іггм = 200mА,
DCR4060V22 DCR4060V20 DCR4060V18	2200 2000 1800	Vdrm, Vrrm t _P = 10ms Vdsm & Vrsm =
		VDRM & VRRM + 100V respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

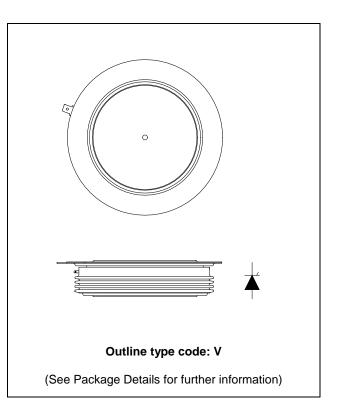
DCR4060V22

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

2200V
4040A
54000A
1500V/µs
300A/µs

* Higher dV/dt selections are available on request







T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	4040	А
It(rms)	RMS value	-	6350	А
Іт	Continuous (direct) on-state current	-	5860	А

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SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C		kA
l²t	I ² t for fusing	VR = 0	14.6	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Parameter Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	7.5	°C/kW
Rth(j-c)	Thermal resistance - junction to case		Anode DC	-	13.0	°C/kW
		Single side cooled	Cathode DC	-	17.8	°C/kW
Back	Thermal registeres access to heateink	Clamping force 54kN (with mounting compound)	Double side	-	2.0	°C/kW
Ktn(c−n)	Rth(c-h) Thermal resistance - case to heatsink		Single side	-	4.0	°C/kW
Τvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range	perature range		-55	125	°C
Fm	Clamping force			48	59	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	IS	Min.	Max.	Units
Irrm/Idrm	Peak reverse and off-state current	At Vrrm/Vdrm, Tcase = 125°C	;	-	200	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.15	1.30	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Tj = 125°C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x IT(AV) Gate source 30V, 10Ω	Repetitive 50Hz	-	150	A/µs
avat		$tr < 0.5 \mu s, T_j = 125^{\circ}C$	Non-repetitive	-	300	A/µs
	Threshold voltage - Low level	500A to 2300A at T _{case} = 125°C		-	0.78	V
V τ(το)	Threshold voltage - High level	2300A to 7000A at T _{case} = 125°C		-	0.92	V
	On-state slope resistance - low level	500A to 2300A at T _{case} = 125°C		-	0.16	mΩ
ľΤ	On-state slope resistance - High level	2300A to 7000A at Tcase = 125°C		-	0.10	mΩ
tgd	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω tr = 0.5µs, Tj = 25°C		-	3	μs
tq	Turn-off time	$T_{j} = 125^{\circ}C, V_{R} = 200V, dI/dt = 1A/\mu s,$ $dV_{DR}/dt = 20V/\mu s \text{ linear}$		-	600	μs
Qs	Stored charge	I⊤ = 2000A, Tj = 125°C, dl/dt = 1A/µs		390	1920	μC
Irr	Reverse recovery current	VR(peak) ~ 1300V, VRM ~ 900V		17	36	А
lı.	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ін	Holding current	Тј = 25°С, R _{G-} к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrм = 5V, Tcase = 25°С	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrм = 5V, Tcase = 25°С	250	mA
Igd	Gate non-trigger current	At 50% Vdrм, Tcase = 125°С	10	mA

CURVES

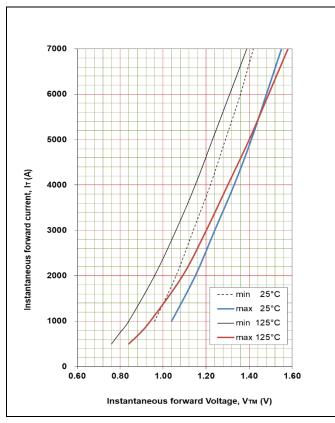


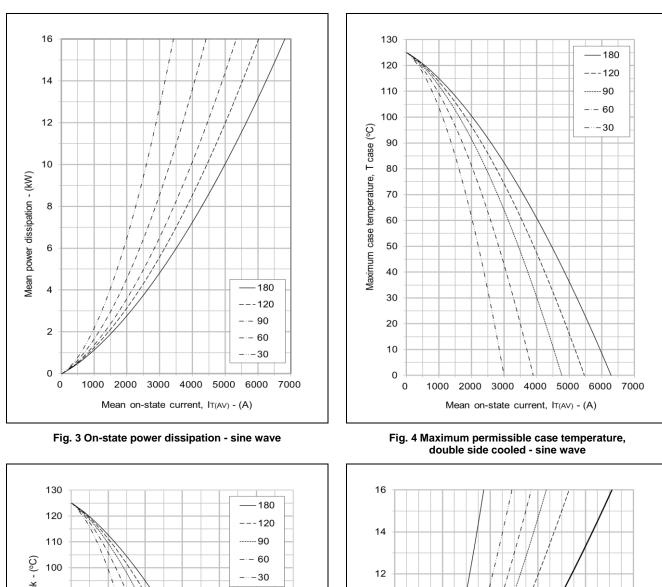
Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

$$V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 0.404689 B = 0.051381 C = 0.000056 D = 0.003938 These values are valid for $T_j = 125^{\circ}C$ for I_T 500A to 7000A

DCR4060V22



10

8

6

2

0 +

2000

4000

6000

Mean on-state current, IT(AV) - (A)

Fig. 6 On-state power dissipation - rectangular wave

power dissipation - (kW)

4 Mean

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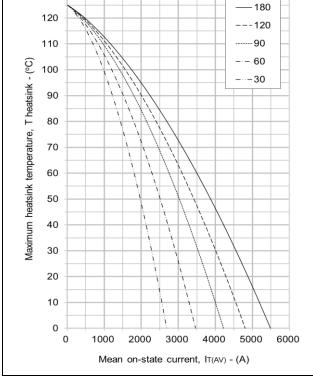


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

10000

d.c

180

120

90

- 60

30

8000

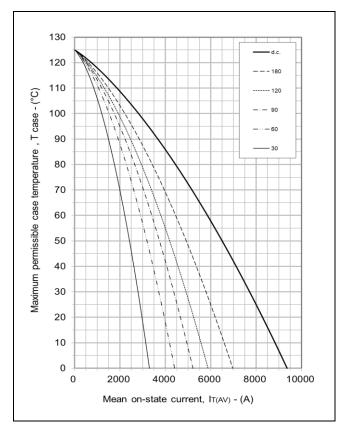
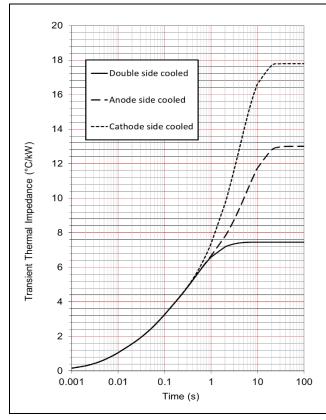


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



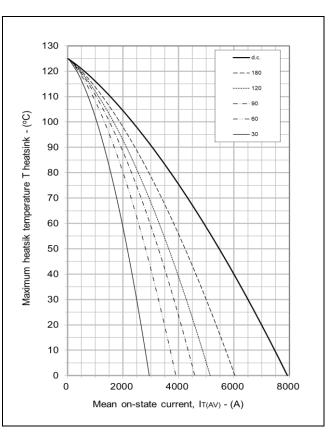


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side cooled	Ri(°C/kW)	0.921	1.830	3.402	1.304
	Ti(s)	0.008	0.058	0.408	1.209
Anode side cooled	Ri(°C/kW)	0.903	1.672	3.010	7.427
	Ti(s)	0.008	0.054	0.314	5.624
Cathode side	Ri(°C/kW)	0.948	2.066	1.688	13.085
cooled	Ti(s)	0.008	0.065	0.389	4.145

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

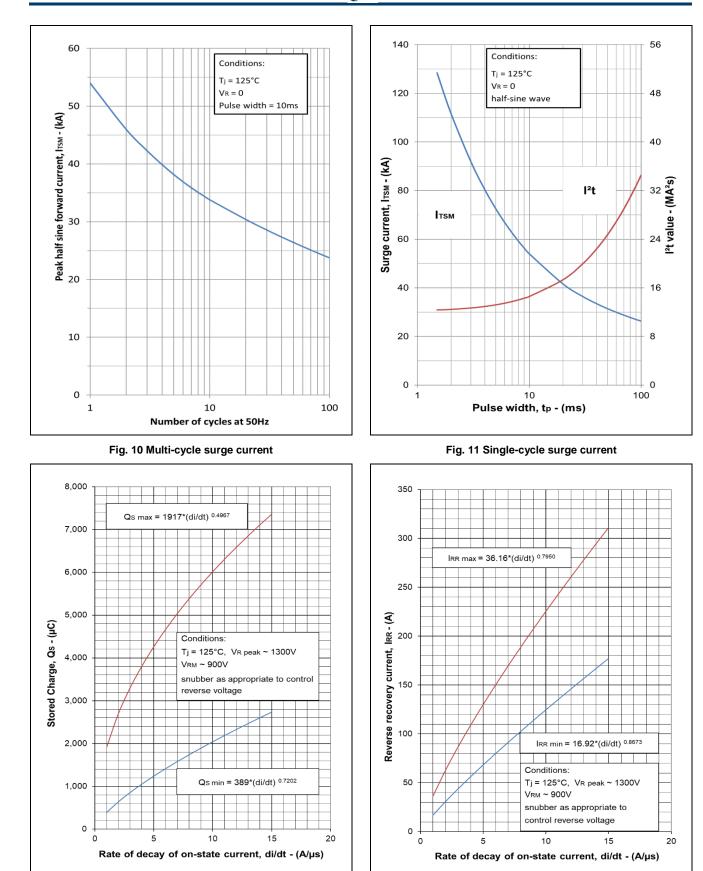
 $\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance R $_{\text{frij-ej}}$ when the device operates at conduction angles other than d.c.

	Double side cooling		Anode Side Cooling		Ca	thode Side	d Cooling	
	ΔZ _{th}	(Z)		ΔZ	2th (Z)		ΔZ	н (Z)
θ°	sine.	rect.	θ°	sine.	rect.	θ°	sine.	rect.
180	1.34	0.88	180	1.34	0.88	180	1.33	0.88
120	1.57	1.30	120	1.57	1.30	120	1.57	1 29
90	1.83	1.54	90	1 84	1.54	90	183	1.53
60	2.08	1.81	60	2.08	1.81	60	2.07	1.80
30	2.27	2.11	30	2.28	2.11	30	2.26	2.10
15	2.36	2.28	15	2.37	2.28	15	2.35	2.26



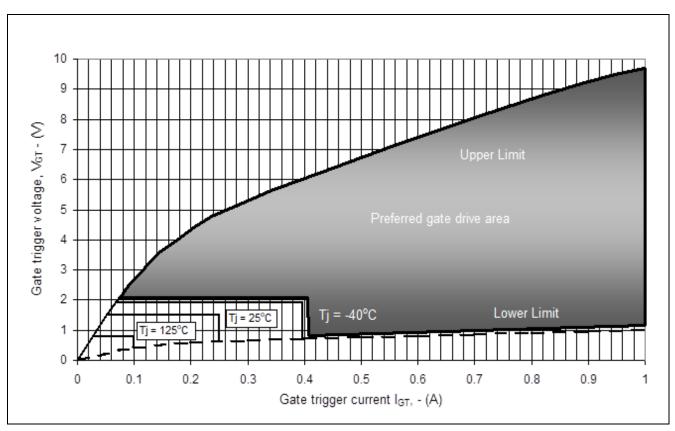
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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Fig. 14 Gate characteristics

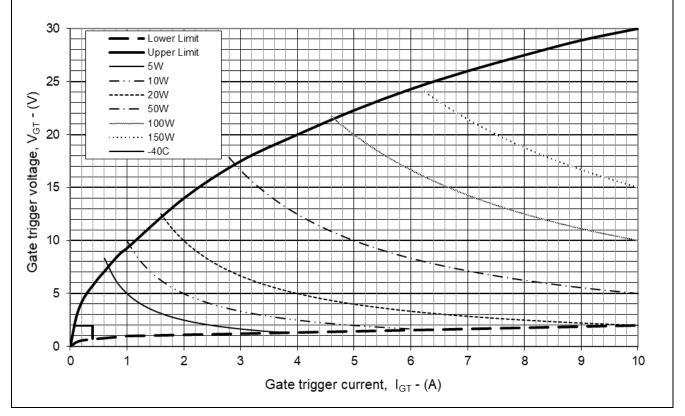


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

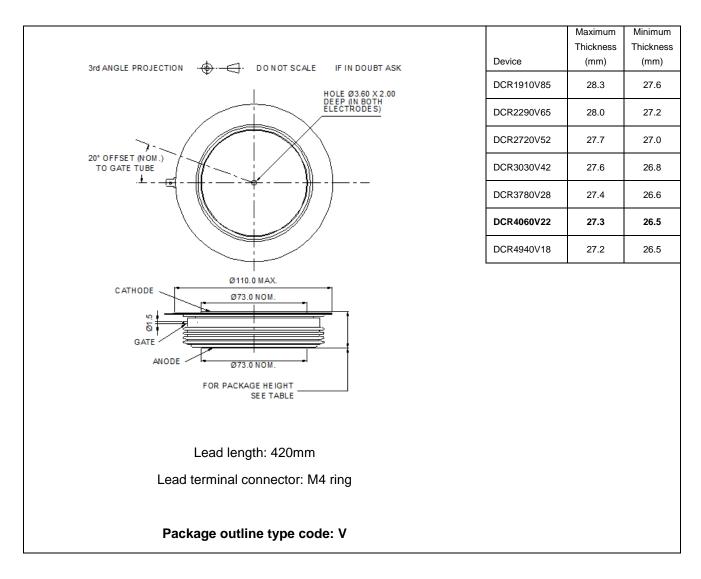


Fig. 16 Package outline

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